Transition between Nonresonant and Resonant Charge Transport in Molecular Junctions

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ABSTRACT: Efficient long-range charge transport is required for high-performance molecular electronic devices. Resonant transport is thought to occur in single molecule junctions when molecular frontier orbital energy levels align with electrode Fermi levels, thereby enabling efficient transport without molecular or environmental relaxation. Despite recent progress, we lack a systematic understanding of the transition between nonresonant and resonant transport for molecular junctions with different chemical compositions. In this work, we show that molecular junctions undergo a reversible transition from nonresonant tunneling to resonant transport as a function of applied bias. Transient bias-switching experiments show that the nonresonant to resonant transition is reversible with the applied bias. We determine a general quantitative relationship that describes the transition voltage as a function of the molecular frontier orbital energies and electrode Fermi levels. Overall, this work highlights the importance of frontier orbital energy alignment in achieving efficient charge transport in molecular devices.

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wires. Despite these observations, we lack a systematic understanding of the transition between nonresonant and resonant transport for junctions with different chemical compositions.

In this work, we study the nonresonant to resonant transition for a series of molecular junctions with different backbone compositions and frontier orbital energies. Interestingly, our results show that the transition voltage ($V_T$) follows a general linear relationship with the molecular frontier orbital energies. Our experimental results are consistent with a general physical model that considers the applied bias, electrode Fermi energies, and the strength and symmetry of the molecule-electrode coupling. Charge transport is characterized in molecular junctions based on para-linked oligophenyls and related control molecules terminated with amine (NH$_2$) and thiomethyl (SMe) anchors. At low applied bias, molecular conductance is length-dependent and decays exponentially as a function of molecular length. Upon increasing the applied bias in a stepwise fashion, remarkably high levels of conductance ($>10^{-2}G_0$) are observed, where $G_0$ is the quantum unit of conductance ($G_0 = 2e^2/h = 77.5 \mu S$). Interestingly, we observe a marked decrease in the length-dependent conductance decay constant ($\beta$) for amine- and thiomethyl-terminated p-terphenyl junctions at applied biases of 1 and 1.75 V, respectively, which suggests a transition from nonresonant to resonant transport. We further studied time-dependent, transient molecular conductance in bias-switching experiments using the holding mode of a scanning tunneling microscope-break junction (STM-BJ) instrument. Bias-switching experiments clearly show that the nonresonant to resonant transition is reversible as a function of applied bias. Taken together, our results show that resonant transport offers an effective approach for achieving efficient long-range transport in molecular junctions.

A series of conjugated molecules was synthesized using reported methods or via iterative cross-coupling with MIDA boronates with automated catch-and-release purification and characterized by $^1$H and $^{13}$C NMR spectroscopy (Supporting Information, Figures S1–S3). Following synthesis, we began by studying the charge transport properties of amine- (Pn-NH$_2$) and thiomethyl- (Pn-SMe) terminated oligophenyls ($n = 1, 2, 3$) attached to gold electrodes (Figure 1a) using a custom-built STM-BJ instrument, as previously described. In particular, we determined molecular conductance for Pn-NH$_2$ and Pn-SMe oligophenyls (0.01 mM - 0.1 mM in 1,2,4-trichlorobenzene) as a function of applied bias. One-dimensional (1D) average conductance histograms for P1-NH$_2$, P2-NH$_2$, and P3-NH$_2$ and P1-SMe, P2-SMe, and P3-SMe across a wide range of applied biases (-1.9 V to +1.9 V) are shown in Figures S4 and S5, respectively. The stability of molecular junctions across this range of applied bias is confirmed using transient, time-dependent conductance measurements using the holding mode of STM-BJ, as described below. Peak conductance values for Pn-NH$_2$ and Pn-SMe are plotted on a semilog scale against the applied bias in Figure 1b and Figure S6. Overall, molecular conductance plots for Pn-NH$_2$ and Pn-SMe are symmetric with respect to applied bias in the nonpolar solvent 1,2,4-trichlorobenzene.31

Remarkably, our results show that P3-NH$_2$ and P3-SMe exhibit an abrupt jump in conductance at applied biases of 1 and 1.75 V, respectively (Figure 1b). In general, all molecular junctions based on Pn-NH$_2$ and Pn-SMe show high conductance values above $10^{-2}G_0$ under high applied biases.
Using a quantum tunneling model such that $G/G_0 = A \exp (-\beta L)$, where $A$ is a prefactor related to contact conductance, $\beta$ is the molecular decay constant, and $L$ is the molecular length between terminal carbon atoms in the junction, we determined molecular decay constants $\beta$ for Pn-NH$_2$ and Pn-SMe as a function of applied bias. Our results show that the molecular decay constants are $\beta = 0.41 \pm 0.01$ Å$^{-1}$ (Pn-NH$_2$) and $\beta = 0.39 \pm 0.03$ Å$^{-1}$ (Pn-SMe) at 0.25 V for oligophenyls, which is consistent with acetylene-terminated$^6$ ($\beta = 0.38 \pm 0.03$ Å$^{-1}$) and trimethyltin-terminated$^7$ ($\beta = 0.43$ Å$^{-1}$) oligophenyls. Surprisingly, we observe a abrupt decrease in $\beta$ for P3-NH$_2$ at 1 V and P3-SMe at 1.75 V (Figure 1c). Decay constants decrease with increasing applied bias and become nearly length-independent at 1.9 V, such that $\beta = 0.03$ Å$^{-1}$.

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molecules generally show larger displacements compared to Pn-NH$_2$ (Figure 1d). Moreover, the nearly length-independent molecular decay constants $\beta$ at high bias are consistent with a resonant tunneling mechanism for charge transport.

Two-dimensional (2D) conductance histograms show that average molecular displacements at junction breakage increase with molecular length. In particular, 2D conductance histograms for Pn-NH$_2$ and Pn-SMe at low bias (0.25 V) and high bias (1.9 V) are shown in Figures S7 and S8. Interestingly, Pn-SMe molecules generally show larger displacements compared to Pn-NH$_2$ counterparts, which is consistent with prior work and is attributed to a weaker force constant between Au and SMe anchors. Our results further show that Pn-SMe exhibits a slightly larger conductance than Pn-NH$_2$ at 0.25 V (Figure 1d), which agrees with prior work and is attributed to stronger coupling between SMe-terminated molecules and Au d-orbitals. Unexpectedly, we observe that the conductance order is reversed at high bias, such that Pn-NH$_2$ molecules show significantly larger conductance values than Pn-SMe molecules above 1 V (Figure 1b and Figure S6), which is especially apparent for biphenyl or p-terphenyl junctions.

Electrochemical reactions in molecular junctions have been shown to result in conductance enhancements at high applied bias. In prior work, Zang et al. reported the formation of Au–N covalent bonds for P3-NH$_2$ due to electrochemical reactions at high bias, which leads to a high conductance state. To exclude the possibility of electrochemical-induced reactions at high applied bias, we performed time-dependent, transient measurements of molecular conductance using the holding mode of operation of the STM-BJ instrument. Here, a single molecule junction is held at a constant displacement while changing the applied bias and directly measuring conductance (Figure 2). The experiment is performed by holding a single molecule under low applied bias (0.5 V) for the initial phase (65 ms), followed by a step increase in the applied bias (1.25 V for P3-NH$_2$ and 1.9 V for P3-SMe) for 60 ms, after which the bias is returned to the initial level (0.5 V). Figures 2c–d clearly show that the molecular conductance is reversible under controlled bias ramps. In particular, molecular conductance returns to similar levels as the initial low bias after the step change in applied bias. Overall, these results indicate that the transition or jump in molecular conductance is reversible, which strongly suggests that the molecular structures do not undergo electrochemical reactions under high applied bias.

To understand the transition bias from nonresonant to resonant transport, we performed a series of single molecule conductance experiments by increasing the bias voltage in small steps in the vicinity of the conductance jump (Figure 3). In the vicinity of the conductance jump for both P3-NH$_2$ (Figure 3c) and P3-SMe (Figure 3g), 1D and 2D conductance histograms clearly show two underlying molecular subpopulations with different conductance values. However, at low bias, the 2D conductance plots only show the low-conductance subpopulation (Figure 3b,f), whereas at high bias, the 2D conductance plots show only the high conductance subpopulation (Figure 3d,h). Upon increasing the applied bias from 0.75 to 1.25 V, the overall shape of the conductance plateau for P3-NH$_2$ in 2D conductance histograms shifts from a downward slope to a nearly flat horizontal shape (Figure 3b–d). We attribute this phenomenon to the shift from length-dependent nonresonant tunneling to nearly length-independent resonant transport. Our results suggest that two distinct conductance states exist for P3-NH$_2$ and P3-SMe, and the charge transport mechanism changes from nonresonant tunneling to resonant tunneling at transition voltages ($V_{\text{tr}}$) corresponding to $\sim$1 V for P3-NH$_2$ and $\sim$1.625 V for P3-SMe, respectively. Here, we emphasize that the transition voltage ($V_{\text{tr}}$) for resonant transport is different than the transition voltage ($V_{\text{trans}}$) in transition voltage spectroscopy (TVS) which measures the transition from a trapezoidal barrier at low bias (Simmons tunneling) to a triangular barrier at high bias (Fowler-Nordheim tunneling). Typically, $V_{\text{trans}}$ is determined as the inflection point on a plot of $\ln$ ($G/V$) versus $1/V$. The calculated $V_{\text{trans}}$ for P3-SMe is less than 1 V, which is lower than $V_{\text{tr}}$ for resonant transport (Figure S9).

Prior work has shown that high bias can affect molecular conformations. In general, molecules with planar conformations exhibit larger average conductance values compared to their nonplanar or twisted counterparts. To investigate whether a bias-induced conformational change leads to a conductance jump, we synthesized a control molecule (P3-planar) with a “locked” and fully planar backbone conformation and determined conductance as a function of applied bias (Figure S10a). Interestingly, our results show that the conductance-voltage plot of P3-planar follows the same trends as P3-SMe (Figure S10b), and P3-planar exhibits a transition voltage $V_{\text{t}}$ around 1.625 V (Figure S10c). At low bias (0.25 V), P3-planar shows a higher conductance than P3-NH$_2$ and P3-SMe due to the planar conformation. However, at high applied bias immediately following the conductance jump for P3-NH$_2$ ($\sim$1 V), the conductance of P3-NH$_2$ is significantly larger than P3-planar, which indicates that the conductance jump does not result from molecular conformational changes, and the fully planar molecule (P3-planar) undergoes a nonresonant to resonant transition in transport.

To further understand the voltage-dependent conductance response of P3-NH$_2$ and P3-SMe, we performed molecular modeling using nonequilibrium Green’s function-density functional theory (NEGF-DFT) via the Atomistix Toolkit package. Molecular geometries for P3-NH$_2$ and P3-SMe are optimized using DFT calculations performed on Spartan’16 Parallel Suite using the B3LYP functional with a 6-31G (d,p) basis set. Following determination of geometry-optimized structures, transmission functions and conductance-voltage ($G$–$V$) plots are calculated using NEGF-DFT (Figure S11). Our results show that the HOMO energy level of P3-NH$_2$ is closer to the Fermi energy level $E_F$ compared to P3-SMe (Figure S11b), and conductance jumps from simulations occur at $\sim$1.25 V for P3-NH$_2$ and $\sim$1.5 V for P3-SMe, respectively (Figure S11c). The conductance of P3-NH$_2$ increases by a factor of $\sim$30 when the voltage changes from 0.5 V (nonresonant transport) to 1.5 V (resonant transport). The enhancement ratio in molecular conductance for P3-NH$_2$ is consistent with experimental results (Figure 1b). Overall, the calculated G-V curves are in qualitative agreement with the experimental results, although the positions and magnitudes of the conductance jumps are only qualitatively consistent with experimental values due to the asymmetry of electrodes and the level of DFT theoretical framework.

On the basis of these observations, we sought to develop a general quantitative description for the nonresonant to resonant transition voltage $V_{\text{tr}}$ as a function of molecular properties. The transition voltage for resonant transport is thought to primarily depend on the alignment between the dominant frontier orbital energy and the gold electrode Fermi energy. To systematically understand the relationship between
the transition voltage and frontier orbitals, we experimentally characterized molecular conductance for a series of junctions with different molecular compositions and correspondingly different HOMO and LUMO frontier energy levels (Figure 4). Specifically, we determined the conductance of 4′-(methylthio)-[1,1′:4,1″-terphenyl]-4-amine (NH2-P3-SMe), p-terphenyl-4,4″-dithiol (P3-SH), 1,4-di(pyridin-4-yl)benzene (P3-Py), and 4,4″-diethynyl-1,1′:4′,1″-terphenyl (P3-Ace) as a function of applied bias (Figure 4a and Figures S12−S13). Our results show that the conductance values of P3-SH, P3-Py, and P3-Ace smoothly and gradually increase upon increasing the applied bias without abrupt jumps, as shown in Figure 4b and Figure S13. In general, the choice of anchors affects the electronic coupling at the electrode-molecule interface. Strong electronic coupling will induce broadening of the HOMO and LUMO levels, which leads to a smooth and continuous transition from nonresonant to resonant transport.40 Transmission functions for P3-SH, P3-Py, and P3-Ace were calculated using NEGF-DFT (Figure S14). Interestingly, we observe broad resonance states for P3-SH, P3-Ace, and P3-Py located close to the Fermi level (within ±0.5 eV). Strong electronic coupling between electrodes and anchors (thiol, acetylene, and pyridine) generally explains the absence of an abrupt conductance jump for these molecules. P3-NH2, NH2-P3-SMe, and P3-SMe show abrupt jumps in molecular conductance at specific applied biases (Figure 4b). Unexpectedly, the conductance of P3-NH2 and NH2-P3-SMe is larger than P3-SH at high applied bias (>1 V) after both molecules exhibit an abrupt jump in conductance (Figure 4b). In addition, the transition voltages $V_T$ for nonresonant to resonant transport are vastly different for P3-NH2, NH2-P3-SMe, and P3-SMe, which suggests that $V_T$ depends on molecular composition.

To further understand the molecular conductance data, we plotted the transition voltage $V_T$ as a function of the HOMO energy levels for a series of conjugated organic molecules (Figure 4c and Table S1). Interestingly, our results show that the transition voltage $V_T$ decreases with increasing HOMO energy levels ($E_{HOMO}$), following a linear relationship given by

$$0.625 eV_T = -E_{HOMO} - 4.375 eV$$

where $e$ is the charge on an electron. To assess the generality of the linear relationship between $V_T$ and $E_{HOMO}$ given by eq 1, we further characterized the conductance and transition voltages for 4T and (DPPTT)$_n$ with different backbone compositions, lengths, and HOMO energy levels (Figure 4a,c, Table S1, and Figures S15−S17). Interestingly, the transition voltages of these molecules are well described by the general relation, which supports the notion that the linear relationship between $V_T$ and $E_{HOMO}$ can be used to describe resonant transport in conjugated organic molecules.

To understand the physics governing the relationship between the transition voltage and the frontier energy levels, we consider a simple model for a molecular junction with two
gold electrodes (Figure 4d). When the Fermi energy of the gold electrodes $E_F$ is located between the HOMO and LUMO levels, the chemical potentials of the left and right electrodes are given by $E_p = -\eta V_b$ and $E_p + (1 - \eta) eV_b$, respectively, where $V_b$ is the bias voltage and the parameter $\eta$ is related to the strength and symmetry of the molecule-electrode coupling, such that $\eta = 0.5$ for ideal, fully symmetric junctions. To achieve resonant transport in HOMO-conducting molecules, the chemical potential of one electrode aligns with the HOMO energy level such that $E_p = \eta E_{\text{HOMO}}$. In this way, a simple linear relationship is used to relate the HOMO energy and transition voltage such that $\eta eV_T = -E_{\text{HOMO}} + E_p$. Using this expression to analyze our experimental results, we determine the parameters $\eta = 0.625$ and $E_p = -4.375$ eV, respectively. Prior studies reported that the work function of a clean Au surface is 5.1 eV in a vacuum; however, the adsorption of molecules decreases the work function in the range of $\approx 4.2$–$4.4$ eV, as previously reported. In general, the calculated value of the Fermi level of gold $E_F$ from our experiments is consistent with prior work.

The linear relationship describing the transition voltage $V_T$ given by eq 1 is practically useful in designing molecular junctions to achieve resonant transport. In theory, our work suggests that efficient long-range transport can be achieved at low bias when the molecular HOMO energy is close to $-4.375$ eV. Recently, unusual length-independent conductance behaviors were reported for $[n]$cumulenes and porphyrins, which may be related to coherent transport mechanisms in conjugated systems. In addition to conjugated molecules, Porath et al. reported that 10.4 nm long, double-stranded DNA molecules behave like insulators at low bias and efficient conductors at high bias, such that the enhanced conductance was attributed to the alignment between the frontier molecular energy levels and $E_p$. However, nonconjugated molecules such as DNA typically have a large energy mismatch between the HOMO level and $E_p$, making it challenging to observe resonant transport given the bias range of our setup. Nevertheless, electrochemical gating and selection of solvents can be used to modulate the alignment of the conducting frontier orbital relative to the Fermi energy of the electrode, which presents exciting new avenues to understand and control resonant transport in molecular junctions.

In summary, we used a series of single molecule experiments to understand the transition between nonresonant and resonant transport in single molecule junctions. Overall, these results deepen our understanding of the relationship between molecular frontier orbitals and applied bias in single molecule junctions. Broadly, our work holds the potential to aid in the design of new materials and devices for molecular electronics and circuits.

**ASSOCIATED CONTENT**

Supporting Information

The Supporting Information is available free of charge at https://pubs.acs.org/doi/10.1021/acs.nanolett.1c02915.

Description of chemical synthesis of P2-SMe, P3-SMe, NH$_2$-P3-SMe, P3-planar, experimental details on STM-BJ (PDF)

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**Author Contributions**

S.L. conceived the study, carried out STM-BJ measurements, and performed theoretical calculations. H.Y., N.A., and E.R.J. synthesized and characterized the compounds. J.L. and B.L. helped with data analysis. C.M.S., J.S.M., and M.D.B. supervised the research. The manuscript was written by S.L. and C.M.S. with contributions from all other authors.

**Notes**

The authors declare no competing financial interest.

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